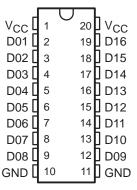
- Designed to Reduce Reflection Noise
- Repetitive Peak Forward Current to 200 mA
- 16-Bit Array Structure Suited for Bus-Oriented Systems
- Package Options Include Plastic Small-Outline Packages and Standard Plastic 300-mil DIPs

description

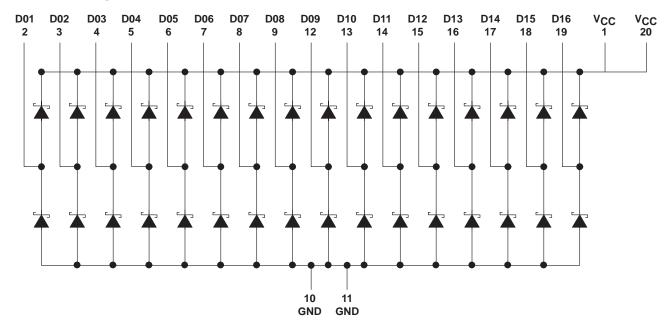
This Schottky barrier diode bus-termination array is designed to reduce reflection noise on memory bus lines. This device consists of a 16-bit high-speed Schottky diode array suitable for clamping to V_{CC} and/or GND.

The SN74S1053 is characterized for operation from 0°C to 70°C .

DW OR N PACKAGE (TOP VIEW)



schematic diagrams





Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)

| Steady-state reverse voltage, V _R | 7 V |
|--|----------------|
| Continuous forward current, I _F : Any D terminal from GND or to V _{CC} | |
| Total through all GND or V _{CC} terminals | 170 mA |
| Repetitive peak forward current [‡] , I _{FRM} : Any D terminal from GND or V _{CC} | 200 mA |
| Total through all GND or V _{CC} terminals | 1.2 A |
| Continuous total power dissipation at (or below) 25°C free-air temperature (see Note 1) | 625 mW |
| Operating free-air temperature range | 0°C to 70°C |
| Storage temperature range, Tota | -65°C to 150°C |

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

single-diode operation (see Note 2)

| | PARAMETER | TEST C | MIN | TYP§ | MAX | UNIT | |
|-------------------------|---------------------------|--------------------|-------------------------|------|------|------|-----|
| V- Ctati | | To Vas | I _F = 18 mA | | 0.85 | 1.05 | |
| | Static forward voltage | To V _{CC} | I _F = 50 mA | | 1.05 | 1.3 | V |
| VF | vp Static forward voltage | From GND | I _F = 18 mA | | 0.75 | 0.95 | V |
| | | FIOIII GIND | I _F = 50 mA | | 0.95 | 1.2 | |
| VFM | Peak forward voltage | | I _F = 200 mA | | 1.45 | | V |
| 10 | Static reverse current | To V _{CC} | V _R = 7 V | | | 5 | |
| ^I R | Static reverse current | From GND | vR = 7 v | | | 5 | μA |
| C. | Total capacitance | $V_R = 0 V$, | f = 1 MHz | | 8 | 16 | nE. |
| C _t Total of | тотат сараспансе | $V_{R} = 2 V$ | f = 1 MHz | · | 4 | 8 | pF |

[§] All typical values are at V_{CC} = 5 V, T_A = 25°C.

NOTE 2: Test conditions and limits apply separately to each of the diodes. The diodes not under test are open-circuited during the measurement of these characteristics.

multiple-diode operation

| | PARAMETER | TEST CO | MIN TY | P [‡] MAX | UNIT | |
|--------------------------------------|-----------------------------|--|------------|--------------------|---------|-----|
| I _X Internal crosstalk cu | Internal grountally ourrent | Total I _F current = 1 A, | See Note 3 | | 0.8 2 | m ^ |
| | Internal crosstalk current | Total I _F current = 198 mA, | See Note 3 | C | .02 0.2 | mA |

[§] All typical values are at $V_{CC} = 5 \text{ V}$, $T_A = 25^{\circ}\text{C}$.

NOTE 3: I_X is measured under the following conditions with one diode static, and all others switching:

Switching diodes: t_W = 100 μs , duty cycle = 20%

Static diode: V_R = 5 V

The static diode input current is the internal crosstalk current Ix.

switching characteristics, $T_A = 25^{\circ}C$ (see Figures 1 and 2)

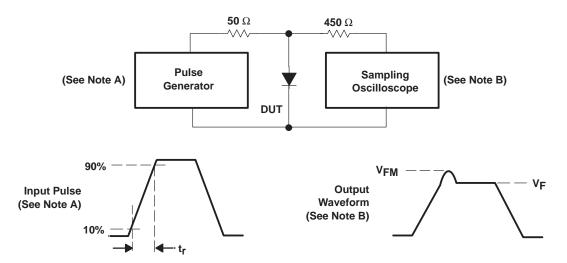
| | PARAMETER | | TEST CON | MIN | TYP | MAX | UNIT | | |
|-----------------|-----------------------|------------------------|--------------------------------|------------------------------|--------------------|-----|------|----|----|
| t _{rr} | Reverse recovery time | $I_F = 10 \text{ mA},$ | $I_{RM(REC)} = 10 \text{ mA},$ | $I_{R(REC)} = 1 \text{ mA},$ | $R_L = 100 \Omega$ | | 8 | 16 | ns |



[‡] These values apply for $t_W \le 100 \mu s$, duty cycle $\le 20\%$.

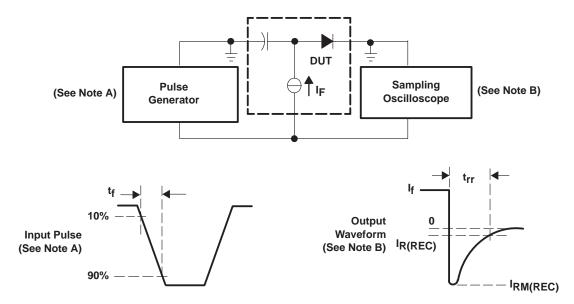
NOTE 1: For operation above 25°C free-air temperature, derate linearly at the rate of 5 m/W/°C.

PARAMETER MEASUREMENT INFORMATION



- NOTES: A. The input pulse is supplied by a pulse generator having the following characteristics: $t_f = 20$ ns, $Z_O = 50 \Omega$, freq = 500 Hz, duty cycle = 1%.
 - B. The output waveform is monitored by an oscilloscope having the following characteristics: $t_{\Gamma} \le 350$ ps, $R_i = 50 \Omega$, $C_i \le 5$ pF.

Figure 1. Forward Recovery Voltage



- NOTES: A. The input pulse is supplied by a pulse generator having the following characteristics: $t_f = 0.5$ ns, $Z_O = 50 \Omega$, $t_W \ge 50$ ns, duty cycle = 1%.
 - B. The output waveform is monitored by an oscilloscope having the following characteristics: $t_{\Gamma} \le 350$ ps, $R_i = 50 \Omega$, $C_i \le 5$ pF.

Figure 2. Reverse Recovery Time

APPLICATION INFORMATION

Large negative transients occurring at the inputs of memory devices (DRAMs, SRAMs, EPROMs, etc.) or on the CLOCK lines of many clocked devices can result in improper operation of the devices. The SN74S1053 diode termination array helps suppress negative transients caused by transmission-line reflections, crosstalk, and switching noise.

Diode terminations have several advantages when compared to resistor termination schemes. Split resistor or Thevenin equivalent termination can cause a substantial increase in power consumption. The use of a single resistor to ground to terminate a line usually results in degradation of the output high level, resulting in reduced noise immunity. Series damping resistors placed on the outputs of the driver reduce negative transients, but they also can increase propagation delays down the line, as a series resistor reduces the output drive capability of the driving device. Diode terminations have none of these drawbacks.

The operation of the diode arrays in reducing negative transients is explained in the following figures. The diode conducts current when the voltage reaches a negative value large enough for the diode to turn on. Suppression of negative transients is tracked by the current-voltage characteristic curve for that diode. Typical current versus voltage curves for the SN74S1053 are shown in Figures 3 and 4.

To illustrate how the diode arrays act to reduce negative transients at the end of a transmission line, the test setup in Figure 5 was evaluated. The resulting waveforms with and without the diode are shown in Figure 6.

The maximum effectiveness of the diode arrays in suppressing negative transients occurs when the diode arrays are placed at the end of a line and/or the end of a long stub branching off a main transmission line. The diodes also can be used to reduce the negative transients that occur due to discontinuities in the middle of a line. An example of this is a slot in a backplane that is provided for an add-on card.

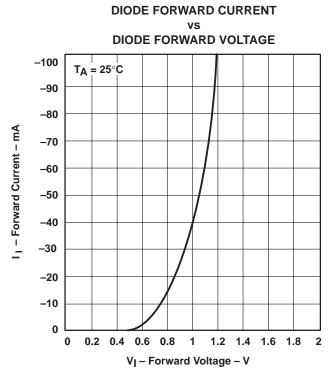


Figure 3. Typical Input Current vs Input Voltage (Lower Diode)



DIODE FORWARD CURRENT DIODE FORWARD VOLTAGE

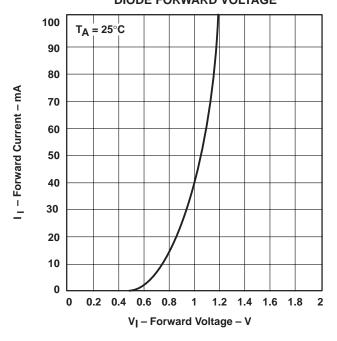


Figure 4. Typical Input Current vs Input Voltage (Upper Diode)

APPLICATION INFORMATION

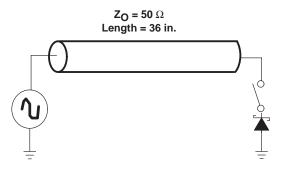


Figure 5. Diode Test Setup

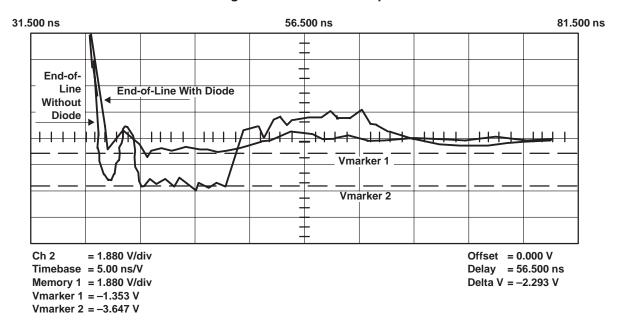


Figure 6. Oscilloscope Display







11-Apr-2013

PACKAGING INFORMATION

| Orderable Device | Status | Package Type | Package Drawing | Pins | Package Qty | Eco Plan | Lead/Ball Finish | MSL Peak Temp | Op Temp (°C) | Top-Side Markings | Samples |
|------------------|--------|--------------|--------------------|------|----------------|----------------------------|------------------|--------------------|--------------|-------------------|---------|
| SN74S1053DBR | ACTIVE | SSOP | DB | 20 | 2000 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | 0 to 70 | S1053 | Samples |
| SN74S1053DBRE4 | ACTIVE | SSOP | DB | 20 | 2000 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | 0 to 70 | S1053 | Samples |
| SN74S1053DBRG4 | ACTIVE | SSOP | DB | 20 | 2000 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | 0 to 70 | S1053 | Samples |
| SN74S1053DW | ACTIVE | SOIC | DW | 20 | 25 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | 0 to 70 | S1053 | Samples |
| SN74S1053DWG4 | ACTIVE | SOIC | DW | 20 | 25 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | 0 to 70 | S1053 | Samples |
| SN74S1053DWR | ACTIVE | SOIC | DW | 20 | 2000 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | 0 to 70 | S1053 | Samples |
| SN74S1053DWRG4 | ACTIVE | SOIC | DW | 20 | 2000 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | 0 to 70 | S1053 | Samples |
| SN74S1053N | ACTIVE | PDIP | N | 20 | 20 | Pb-Free (RoHS) | CU NIPDAU | N / A for Pkg Type | 0 to 70 | SN74S1053N | Samples |
| SN74S1053NE4 | ACTIVE | PDIP | N | 20 | 20 | Pb-Free (RoHS) | CU NIPDAU | N / A for Pkg Type | 0 to 70 | SN74S1053N | Samples |
| SN74S1053NSR | ACTIVE | SO | NS | 20 | 2000 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | 0 to 70 | 74S1053 | Samples |
| SN74S1053NSRG4 | ACTIVE | SO | NS | 20 | 2000 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | 0 to 70 | 74S1053 | Samples |
| SN74S1053PW | ACTIVE | TSSOP | PW | 20 | 70 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | 0 to 70 | S1053 | Samples |
| SN74S1053PWE4 | ACTIVE | TSSOP | PW | 20 | 70 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | 0 to 70 | S1053 | Samples |
| SN74S1053PWG4 | ACTIVE | TSSOP | PW | 20 | 70 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | 0 to 70 | S1053 | Samples |
| SN74S1053PWR | ACTIVE | TSSOP | PW | 20 | 2000 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | 0 to 70 | S1053 | Samples |
| SN74S1053PWRE4 | ACTIVE | TSSOP | PW | 20 | 2000 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | 0 to 70 | S1053 | Samples |
| SN74S1053PWRG4 | ACTIVE | TSSOP | PW | 20 | 2000 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | 0 to 70 | S1053 | Samples |



PACKAGE OPTION ADDENDUM

11-Apr-2013

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) Multiple Top-Side Markings will be inside parentheses. Only one Top-Side Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Top-Side Marking for that device.

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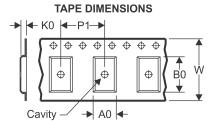
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PACKAGE MATERIALS INFORMATION

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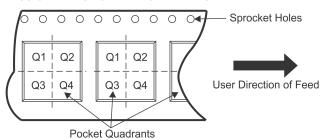
TAPE AND REEL INFORMATION





| _ | | |
|---|----|---|
| | | Dimension designed to accommodate the component width |
| | | Dimension designed to accommodate the component length |
| | | Dimension designed to accommodate the component thickness |
| | W | Overall width of the carrier tape |
| ſ | P1 | Pitch between successive cavity centers |

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

| Device | | Package Drawing | | SPQ | Reel Diameter (mm) | Reel Width W1 (mm) | A0 (mm) | B0 (mm) | K0 (mm) | P1 (mm) | W (mm) | Pin1 Quadrant |
|--------------|-------|--------------------|----|------|--------------------------|--------------------------|------------|------------|------------|------------|-----------|------------------|
| SN74S1053DBR | SSOP | DB | 20 | 2000 | 330.0 | 16.4 | 8.2 | 7.5 | 2.5 | 12.0 | 16.0 | Q1 |
| SN74S1053DWR | SOIC | DW | 20 | 2000 | 330.0 | 24.4 | 10.8 | 13.0 | 2.7 | 12.0 | 24.0 | Q1 |
| SN74S1053NSR | so | NS | 20 | 2000 | 330.0 | 24.4 | 8.2 | 13.0 | 2.5 | 12.0 | 24.0 | Q1 |
| SN74S1053PWR | TSSOP | PW | 20 | 2000 | 330.0 | 16.4 | 6.95 | 7.1 | 1.6 | 8.0 | 16.0 | Q1 |

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*All dimensions are nominal

| Device | Package Type | Package Drawing | Pins | SPQ | Length (mm) | Width (mm) | Height (mm) |
|--------------|--------------|-----------------|------|------|-------------|------------|-------------|
| SN74S1053DBR | SSOP | DB | 20 | 2000 | 367.0 | 367.0 | 38.0 |
| SN74S1053DWR | SOIC | DW | 20 | 2000 | 367.0 | 367.0 | 45.0 |
| SN74S1053NSR | SO | NS | 20 | 2000 | 367.0 | 367.0 | 45.0 |
| SN74S1053PWR | TSSOP | PW | 20 | 2000 | 367.0 | 367.0 | 38.0 |

N (R-PDIP-T**)

PLASTIC DUAL-IN-LINE PACKAGE

16 PINS SHOWN



- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- Falls within JEDEC MS-001, except 18 and 20 pin minimum body length (Dim A).
- The 20 pin end lead shoulder width is a vendor option, either half or full width.



DW (R-PDSO-G20)

PLASTIC SMALL OUTLINE



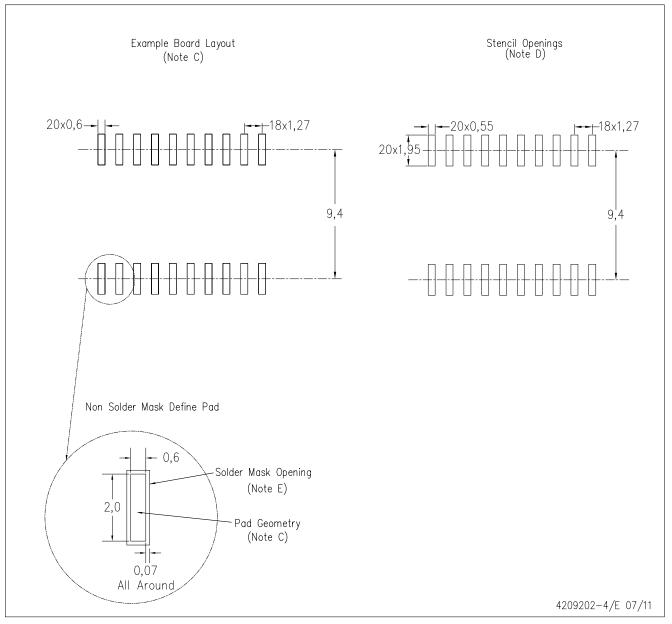
NOTES: A. All linear dimensions are in inches (millimeters). Dimensioning and tolerancing per ASME Y14.5M-1994.

- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion not to exceed 0.006 (0,15).
- D. Falls within JEDEC MS-013 variation AC.



DW (R-PDSO-G20)

PLASTIC SMALL OUTLINE



- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Refer to IPC7351 for alternate board design.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC—7525
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



PW (R-PDSO-G20)

PLASTIC SMALL OUTLINE

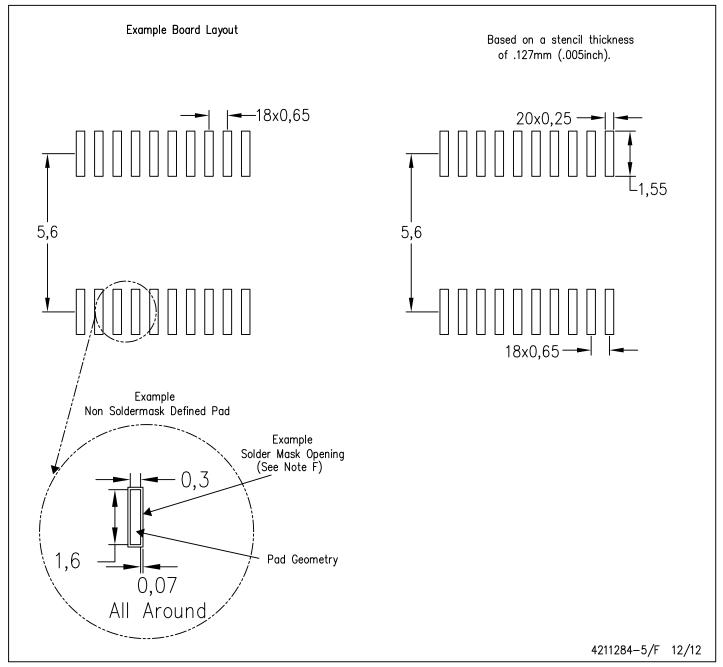


- A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M—1994.
- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0,15 each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0,25 each side.
- E. Falls within JEDEC MO-153



PW (R-PDSO-G20)

PLASTIC SMALL OUTLINE



- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate design.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



MECHANICAL DATA

NS (R-PDSO-G**)

14-PINS SHOWN

PLASTIC SMALL-OUTLINE PACKAGE



- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion, not to exceed 0,15.



DB (R-PDSO-G**)

PLASTIC SMALL-OUTLINE

28 PINS SHOWN



NOTES: A. All linear dimensions are in millimeters.

B. This drawing is subject to change without notice.

C. Body dimensions do not include mold flash or protrusion not to exceed 0,15.

D. Falls within JEDEC MO-150

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